

**1. Scope :**

This specification applies to silicon zerocrossing phototriac chips,  
Device No. ST-2181

**2. Structure :**

- 2-1. Planar type .
- 2-2. Electrodes :aluminum alloy

**3. Size :**

- 3-1. Chip size : 47.2 mils × 47.2 mils (1.200 mm ×1.200mm ).
- 3-2. Chip thickness : 9±1.0 mil (0.230± 0.025 mm ).
- 3-3. Pad area : 5.9 mil × 5.5 mil (0.150 mm ×0.140 mm ).
- 3-4. Pattern drawing : refer to the attached drawing.

**4. Electro-optical characteristics (Ta = 25 °C)**

| Parameter                     | Symbol    | Condition        | Min. | Typ. | Max. | Unit       |
|-------------------------------|-----------|------------------|------|------|------|------------|
| Peak blocking Current         | $I_{DRM}$ | $V_{DRM}=800V$   |      |      | 100  | nA         |
| Peak on-state voltage         | $V_{TM}$  | $I_{TM}=100mA$   |      | 1.7  | 3    | V          |
| Critical rate of Rise voltage | $dv/dt$   |                  | 1000 |      |      | V/ $\mu$ S |
| Holding current               | $I_H$     |                  |      | 350  |      | $\mu$ A    |
| Inhibit Voltage               | $V_{INH}$ | $I_{DS}=10\mu A$ |      | 6    | 20   | V          |

